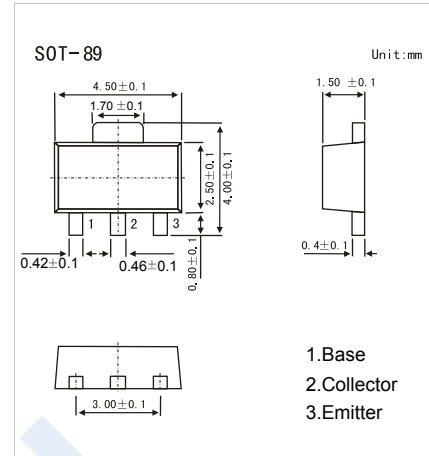


NPN Transistors

KTC4376

■ Features

- 1W (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to KTA1664



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	35	V
Collector - Emitter Voltage	V _{CEO}	30	
Emitter - Base Voltage	V _{EB0}	5	
Collector Current - Continuous	I _c	800	mA
Base Current	I _B	160	
Collector Power Dissipation	P _c	500	mW
		1	W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = 100uA, I _E = 0	35			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = 10 mA, I _B =0	30			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100uA, I _c = 0	5			
Collector-base cut-off current	I _{CB0}	V _{CB} = 35V, I _E = 0			0.1	uA
Emitter cut-off current	I _{EB0}	V _{EB} = 5V, I _c =0			0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =500mA, I _B =20mA			0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =500mA, I _B =20mA			1.2	
Base - emitter voltage	V _{BE}	V _{CE} = 1V, I _c =10mA	0.5		0.8	
DC current gain	h _{FE}	V _{CE} = 1V, I _c =100mA	100		320	
		V _{CE} = 1V, I _c =700mA	35			
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E =0, f=1MHz		13		pF
Transition frequency	f _T	V _{CE} = 5V, I _c = 10mA		120		MHz

■ Classification of h_{FE}(1)

Type	KTC4376-O	KTC4376-Y
Range	100-200	160-320
Marking	PO	PY

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KTC4376

■ Typical Characteristics

